14. The method according to claim 13, wherein a crystal growth of said semiconductor film is laterally and parallel to said substrate.

15. An apparatus according to claim 13, wherein said element is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, and Au.

16. An apparatus according to claim 13, wherein said electronic apparatus is one of a portable intelligent terminal, a head mounted display, a front-projection, a cellular mobile telephone, a portable video camera and a rear-projection

17. An electronic apparatus having an electroluminescence display having at least a P-channel thin film transistor and at least an N-channel thin film transistor, comprising:

semiconductor islands of said P-channel and N-channel thin film transistors comprising silicon over a substrate, each of said semiconductor islands having at least a channel region and source and drain regions and containing an element for promoting crystallization of silicon; and

a gate electrode adjacent to each of said semiconductor islands with a gate insulating film interposed therebetween, said gate electrode comprising at least one of tantalum and titanium,

wherein a concentrations of said element in said source and drain regions is higher than that in the channel region in each of the semiconductor islands.

18. The method according to claim 17, wherein a crystal growth of each of said semiconductor islands is laterally and parallel to said substrate.

19. An apparatus according to claim 17, wherein said element is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, and Au.

20. An apparatus according to claim 17, wherein said electronic apparatus is one of a portable intelligent terminal, a head mounted display, a front-projection, a cellular mobile telephone, a portable video camera and a rear-projection

21. An electronic apparatus having an electroluminescence display comprising:

a semiconductor film comprising silicon over a substrate, said semiconductor film containing an element for promoting crystallization of silicon; and

a gate electrode adjacent to said semiconductor film with a gate insulating film interposed therebetween, said gate electrode comprising at least one of tantalum and titanium,

wherein said semiconductor film has phosphorus introduced regions except for a channel region, and

wherein a concentration of said element in said phosphorus introduced regions is higher than that in the channel region in the semiconductor film..

22. An apparatus according to clam 21, wherein said phosphorus introduced regions are source and drain regions in each of said active layers.

23. An apparatus according to claim 21, wherein said element is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, and Au.

24. An apparatus according to claim 21, wherein said electronic apparatus is one of a portable intelligent terminal, a head mounted display, a front-projection, a cellular mobile telephone, a portable video camera and a rear-projection

25. An electronic apparatus having an electroluminescence display having at least a P-channel thin film transistor and at least an N-channel thin film transistor, comprising:

active layers of said P-channel and N-channel thin film transistors comprising silicon over a substrate, each of said active layers containing an element for promoting crystallization of silicon;

a gate electrode adjacent to each of said active layers with a gate insulating film interposed therebetween, said gate electrode comprising at least one of tantalum and titanium;

wherein each of said active layers has phosphorus introduced regions except for a channel region, and

wherein a concentration of said element in said phosphorus introduced regions is higher than that in the channel region in each of the active regions.

26. An apparatus according to claim 25, wherein said phosphorus introduced regions are source and drain regions in each of said active layers.

27. An apparatus according to claim 25, wherein said element is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, and Au.

28. An apparatus according to claim 25, wherein said electronic apparatus is one of a portable intelligent terminal, a head mounted display, a front-projection, a cellular mobile telephone, a portable video camera and a rear-projection

29. An electronic apparatus having an electroluminescence display comprising:

a semiconductor film comprising silicon over a substrate, said semiconductor film containing an element for promoting crystallization of silicon;

a gate electrode adjacent to said semiconductor film with a gate insulating film interposed therebetween, said gate electrode comprising at least one of tantalum and titanium;

phosphorus introduced regions except for a region to be a channel region in said active layer, and then

a first interlayer insulating film over said semiconductor film and the gate electrode; and

a second interlayer insulating film comprising resinous material over said first interlayer insulating film,

wherein said semiconductor film has phosphorus introduced regions except for a channel region, and

wherein a concentration of said element in said phosphorus introduced regions is higher than that in the channel forming region in the semiconductor film..

30. An apparatus according to claim 29, wherein said element is selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, and Au.

31. An apparatus according to claim 29, wherein said first interlayer insulating film comprises silicon nitride.

32. An apparatus according to claim 29, wherein said second interlayer insulating film comprises a material selected from the group consisting of acrylics, polyimide, polyamide, polyimidamide, and epoxies.

33. An apparatus according to claim 29, wherein said second interlayer insulating film is a multilayer film.

34. An apparatus according to claim 29, wherein said electronic apparatus is one of a portable intelligent terminal, a head mounted display, a front-projection, a cellular mobile telephone, a portable video camera and a rear-projection.--